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28238

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Benjamin A. Haskell et al. Examiner: William D. Coleman
Serial No.: 10/537,644 Group Art Unit: 2823
Filed: June 6, 2005 Docket: G&C 30794.93-US-WO
Title: GROWTH OF REDUCED DISLOCATION DENSITY NON-POLAR GALLIUM NITRIDE BY
HYDRIDE VAPOR PHASE EPITAXY

CERTIFICATE OF MAILING OR TRANSMISSION UNDER 37 CFR 1.8

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on April 27, 2006.

By: Barbara Senty

Name: Barbara Senty

MAIL STOP AMENDMENT
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

We are transmitting herewith the attached:

- ☒ Transmittal sheet, in duplicate, containing a Certificate of Mailing under 37 CFR 1.8.
- ☒ Information Disclosure Statement and Form PTO-1449.
- ☒ Cited Reference(s).
- ☒ Charge the fee in the amount of \$180.00 for the Information Disclosure Statement to the Deposit Account.
- ☒ Return postcard.

Please consider this a **PETITION FOR EXTENSION OF TIME** for a sufficient number of months to enter these papers, if appropriate.

Please charge all fees to Deposit Account No. 50-0494 of Gates & Cooper LLP. A duplicate of this paper is enclosed.

Customer Number 22462
GATES & COOPER LLP
Howard Hughes Center
6701 Center Drive West, Suite 1050
Los Angeles, CA 90045
(310) 641-8797

By: George H. Gates
Name: George H. Gates
Reg. No.: 33,500
GHG/bjs

(PTO TRANSMITTAL - GENERAL)



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INFORMATION DISCLOSURE STATEMENT(37 C.F.R. §1.97(c))

MAIL STOP AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

With regard to the above-identified application, the items of information listed on the enclosed Form 1449 are brought to the attention of the Examiner.

Pursuant to 37 C.F.R. §1.97(c), please charge the amount of \$180.00 to Deposit Account No. 50-0494 of Gates & Cooper LLP for having the items of information listed considered after the mailing date of a first Office Action on-the-merits, but before the mailing date of either a final action under 37 C.F.R. § 1.113, or a Notice of Allowance under 37 C.F.R. § 1.311.

In accordance with 37 C.F.R. §1.98(a)(2), a copy of each foreign patent document and each non-patent document listed on the enclosed Form 1449 is provided.

No representation is made that a reference is "prior art" within the meaning of 35 U.S.C. §§ 102 and 103 and Applicants reserve the right, pursuant to 37 C.F.R. § 1.131 or otherwise, to establish that

the reference(s) are not "prior art". Moreover, Applicants do not represent that a reference has been thoroughly reviewed or that any relevance of any portion of a reference is intended.

Consideration of the items listed is respectfully requested. Pursuant to the provisions of M.P.E.P. 609, it is requested that the Examiner return a copy of the attached Form 1449, marked as being considered and initialed by the Examiner, to the undersigned with the next official communication.

Please direct any response or inquiry to the below-signed attorney at (310) 641-8797.

Respectfully submitted,

GATES & COOPER LLP
Attorneys for Applicant(s)

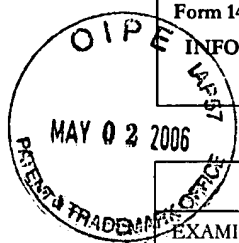
Howard Hughes Center
6701 Center Drive West, Suite 1050
Los Angeles, California 90045
(310) 641-8797

Date: April 27, 2006

GHG/bjs

By: 

Name: George H. Gates
Reg. No.: 33,500



Form 1449*	Docket Number: G&C 30794.93-US-WO	Application Number: 10/537,644
INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION		
Applicant: Benjamin A. Haskell et al.		Filing Date: June 6, 2005
		Group Art Unit: 2823

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
FOREIGN PATENTS							
	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
		T. Gehrke et al., "Pendeo-Epitaxy of Gallium Nitride and Aluminum Nitride Films and Heterostructure on Silicon Carbide Substrate," MRS Internet J. Semicond. Res. 4S1, G3.2, 1999, 6 pp.					
		M. Iwaya et al., "Reduction of Etch Pit Density in Organometallic Vapor Phase Epitaxy-Grown GaN on Sapphire by Insertion of a Low-Temperature-Deposited Buffer Layer Between High-Temperature-Grown GaN," Jpn. J. Appl. Phys., 1998, 37: L316-L318					
		S. Keller et al., "Spiral Growth of InGaN Nanoscale Islands on GaN," Jpn. J. Appl. Phys., 1998, 37: L431-L434					
		P. Kozodoy et al., "Electrical Characterization of GaN <i>p-n</i> Junctions With and Without Threading Dislocations," Appl. Phys. Lett., 1998, 73(7): 975-977					
		S. Nakamura et al., "InGaN/GaN/AlGaN-Based Laser Diodes with Modulation-Doped Strained-Layer Superlattices Grown on an Epitaxially Laterally Overgrown GaN Substrate," Appl. Phys. Lett., 1998, 72(2): 211-213					
		G. Parish et al., "High-Performance (Al,Ga) N-Based Solar-Blind Ultraviolet <i>p-i-n</i> Detectors on Laterally Epitaxially Overgrown GaN," Appl. Phys. Lett., 1999, 75(2): 247-249					
		V. Srikant et al., "Mosaic Structure in Epitaxial Thin Films Having Large Lattice Mismatch," J. Appl. Phys., 1997, 82(9): 4286-4295					
		S. Tanaka et al., "Anti-Surfactant in III-Nitride-Epitaxy - Quantum Dot Formation and Dislocation Termination," Jpn. J. Appl. Phys., 2000, 39: L831-L834					
		S. Tanaka et al., "Self-Assembling GaN Quantum Dots on Al _x Ga _{1-x} N Surfaces Using a Surfactant," Appl. Phys. Lett., 1996, 69(26): 4096-4098					
		A. Usui et al., "Thick GaN Epitaxial Growth with Low Dislocation Density by Hydride Vapor Phase Epitaxy," Jpn. J. Appl. Phys., 1997, 36: L899-L902					

EXAMINER:	DATE CONSIDERED:
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.	